DSF8035SK

Fast Recovery Diode

Replaces March 1998 version, DS4412-1.3

DS4412-2.0 January 2000

APPLICATIONS

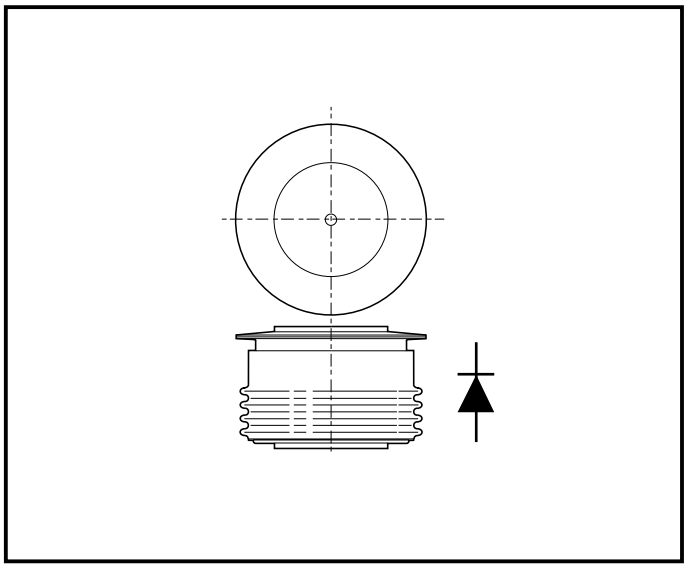
- Snubber Diode For GTO Applications

KEY PARAMETERS

V_{RRM}	3500V
$I_{F(AV)}$	335A
I_{FSM}	3500A
Q_r	400μC
t_{rr}	4.0μs

FEATURES

- Double side cooling
- High surge capability
- Low recovery charge



Outline type code: K.
See Package Details for further information.

VOLTAGE RATINGS

Type Number	Repetitive Peak Reverse Voltage V_{RRM} V	Conditions
DSF8035SK35	3500	$V_{RSM} = V_{RRM} + 100V$

Lower voltage grades available.

CURRENT RATINGS

Symbol	Parameter	Conditions	Max.	Units
Double Side Cooled				
$I_{F(AV)}$	Mean forward current	Half wave resistive load, T_{case} = 65°C	335	A
$I_{F(RMS)}$	RMS value	T_{case} = 65°C	529	A
I_F	Continuous (direct) forward current	T_{case} = 65°C	490	A
Single Side Cooled (Anode side)				
$I_{F(AV)}$	Mean forward current	Half wave resistive load, T_{case} = 65°C	226	A
$I_{F(RMS)}$	RMS value	T_{case} = 65°C	355	A
I_F	Continuous (direct) forward current	T_{case} = 65°C	317	A

SURGE RATINGS

Symbol	Parameter	Conditions	Max.	Units
I_{FSM}	Surge (non-repetitive) forward current	10ms half sine; with 0% $V_{RRM,}$ T_j = 150°C	3.0	kA
I^2t	I^2t for fusing		45×10^3	A^2s
I_{FSM}	Surge (non-repetitive) forward current	10ms half sine; with 50% $V_{RRM,}$ T_j = 150°C	2.4	kA
I^2t	I^2t for fusing		28.8×10^3	A^2s

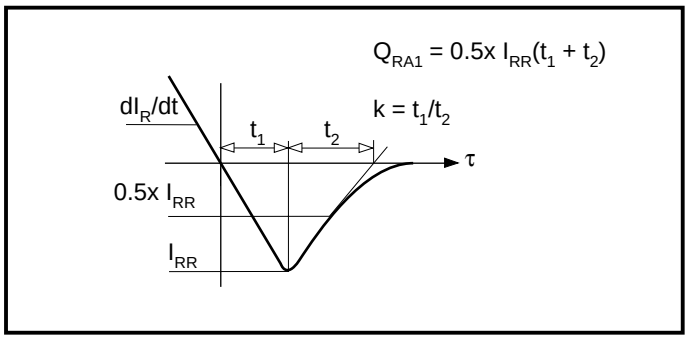
THERMAL AND MECHANICAL DATA

Symbol	Parameter	Conditions		Min.	Max.	Units
$R_{th(j-c)}$	Thermal resistance - junction to case	Double side cooled	dc	-	0.048	°C/W
		Single side cooled	Anode dc	-	0.090	°C/W
			Cathode dc	-	0.103	°C/W
$R_{th(c-h)}$	Thermal resistance - case to heatsink	Clamping force 8.0kN with mounting compound	Double side	-	0.01	°C/W
			Single side	-	0.02	°C/W
T_{vj}	Virtual junction temperature	Forward (conducting)		-	150	°C
T_{stg}	Storage temperature range			-55	175	°C
-	Clamping force			7.0	9.0	kN

CHARACTERISTICS

Symbol	Parameter	Conditions	Typ.	Max.	Units
V_{FM}	Forward voltage	At 400A peak, T_{case} = 25°C	-	3.5	V
I_{RRM}	Peak reverse current	At V_{RRM}, T_{case} = 150°C	-	50	mA
t_{rr}	Reverse recovery time	I_F = 1000A, di_{RR}/dt = 100A/µs T_{case} = 150°C, V_R = 100V	-	4.0	µs
Q_{RA1}	Recovered charge (50% chord)		-	400	µC
I_{RM}	Reverse recovery current		-	220	A
K	Soft factor		1.4	-	-
V_{TO}	Threshold voltage	At T_{vj} = 150°C	-	1.8	V
r_T	Slope resistance	At T_{vj} = 150°C	-	3.7	mΩ
V_{FRM}	Forward recovery voltage	di/dt = 1000A/µs, T_j = 125°C	-	140	V

DEFINITION OF K FACTOR AND Q_{RA1}



CURVES

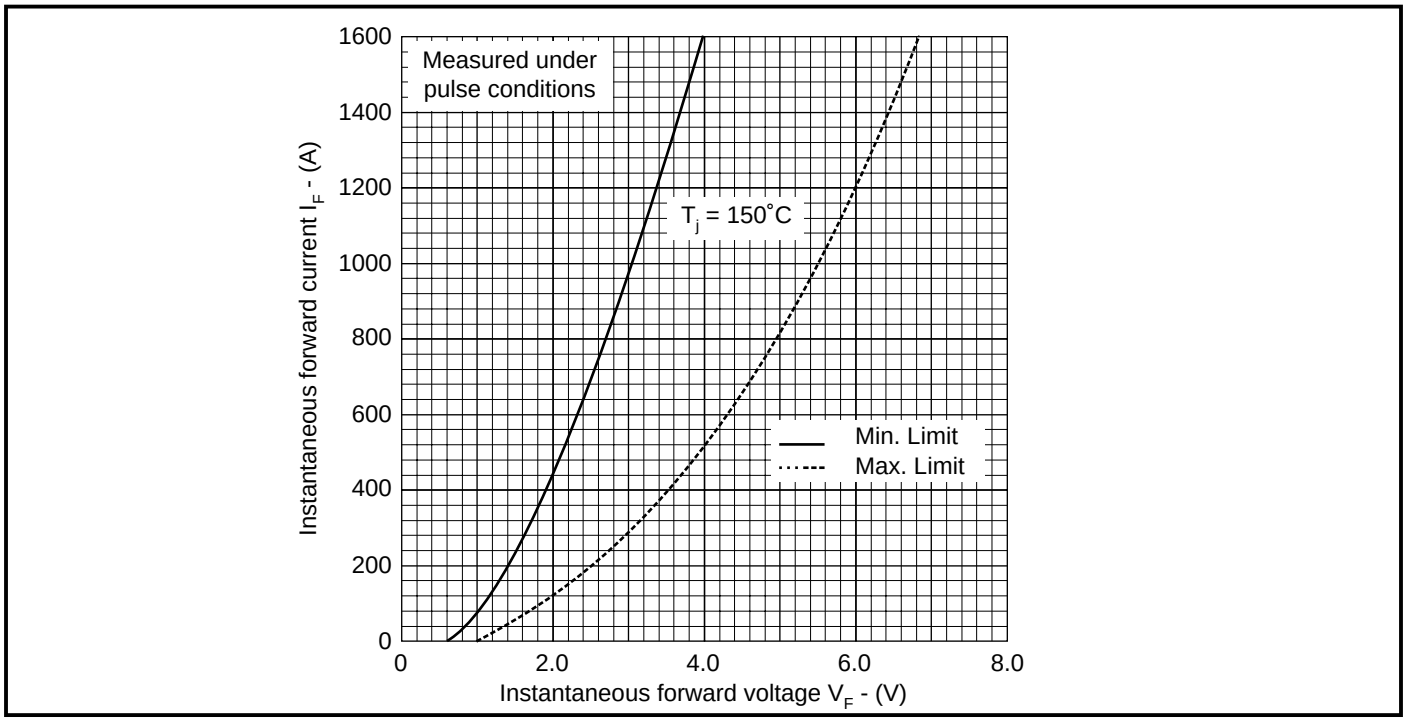


Fig.1 Maximum (limit) forward characteristics

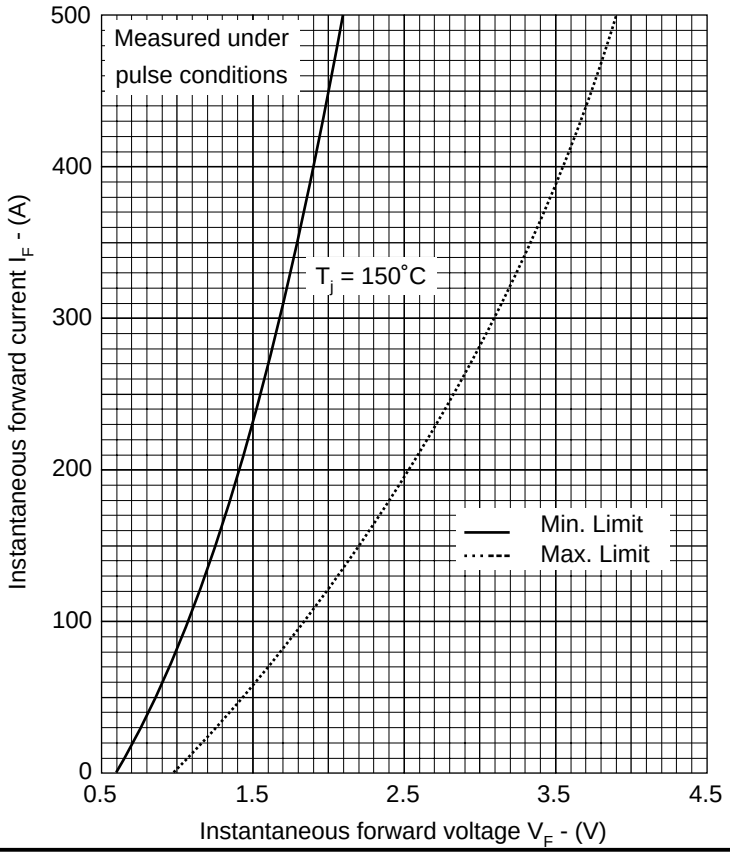


Fig.2 Maximum (limit) forward characteristics

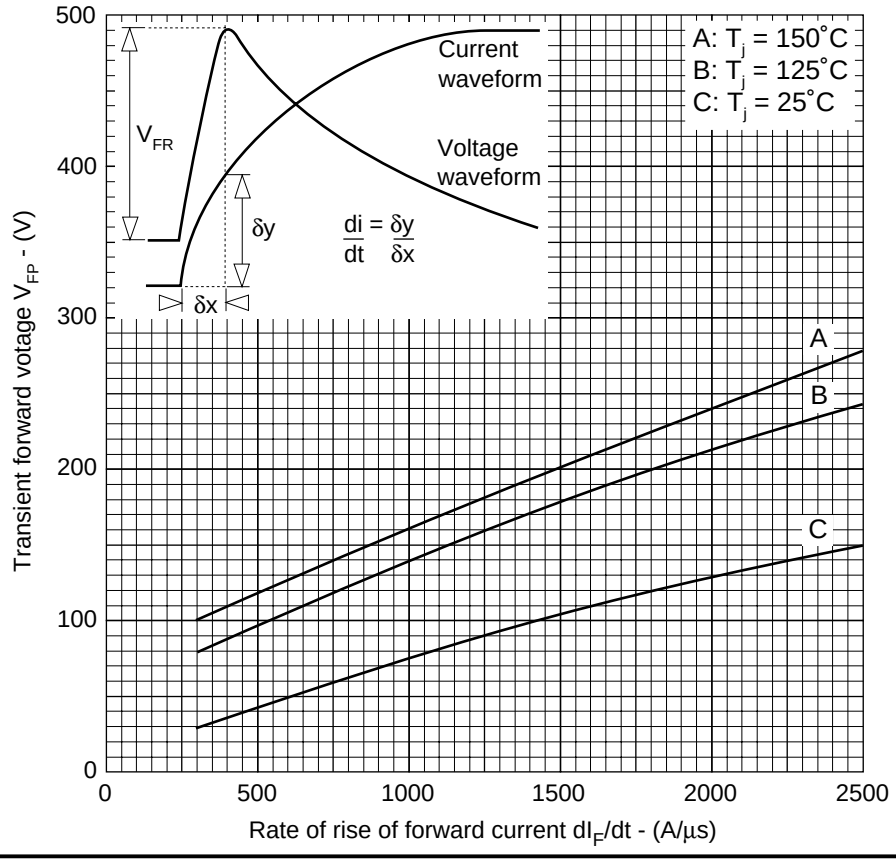


Fig.3 Transient forward voltage vs rate of rise of forward current

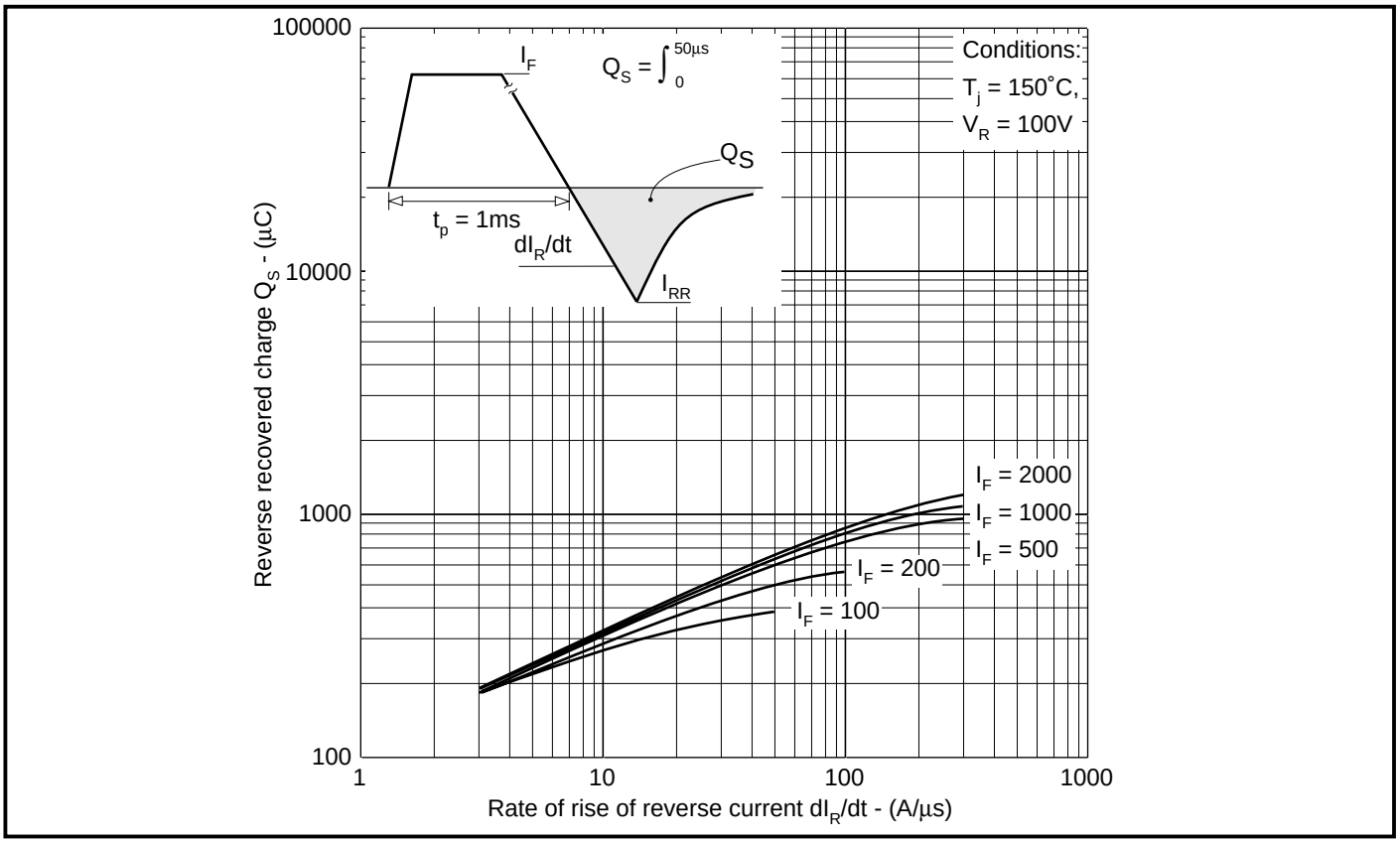


Fig. 4 Recovered charge

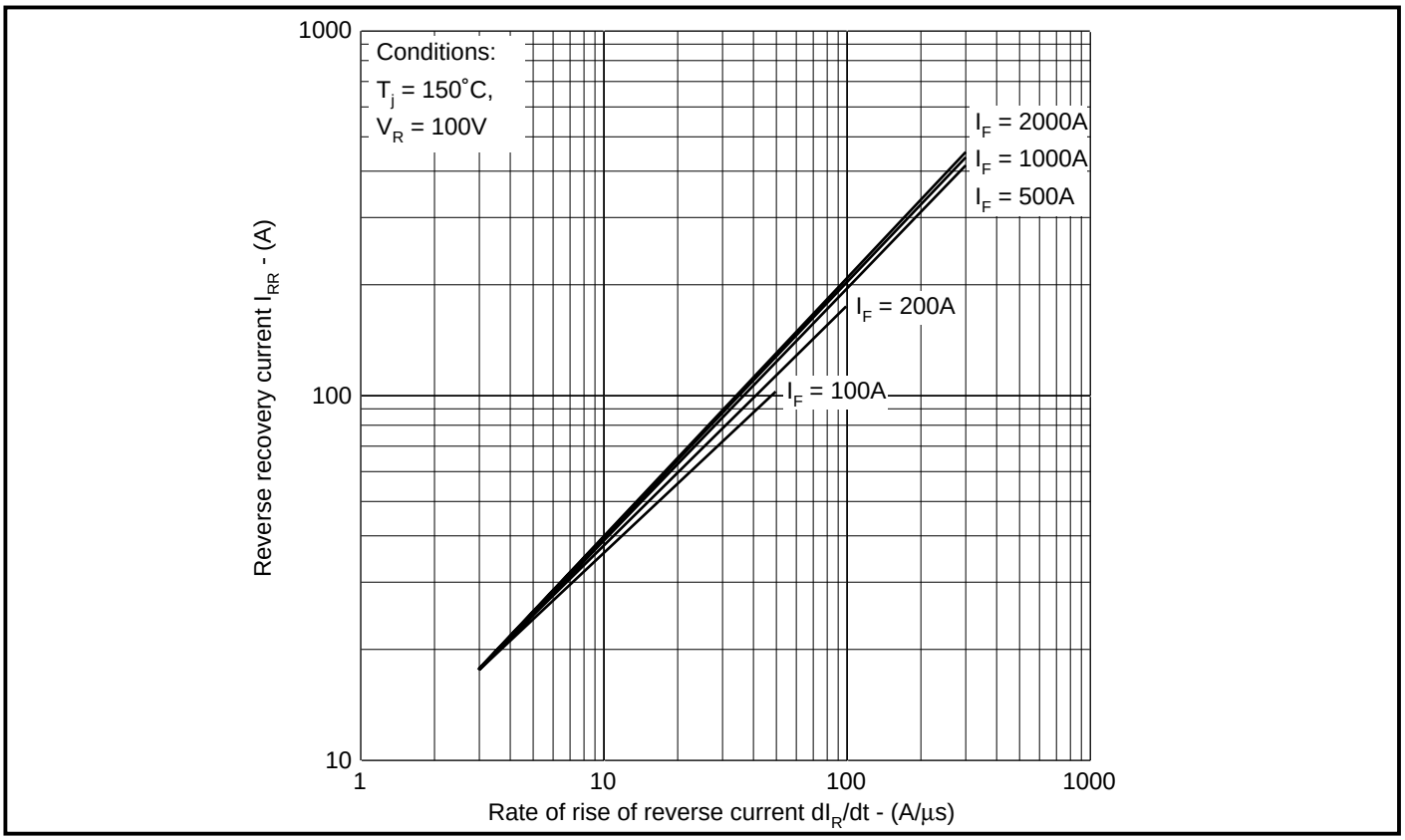


Fig. 5 Typical reverse recovery current vs rate of rise of reverse current

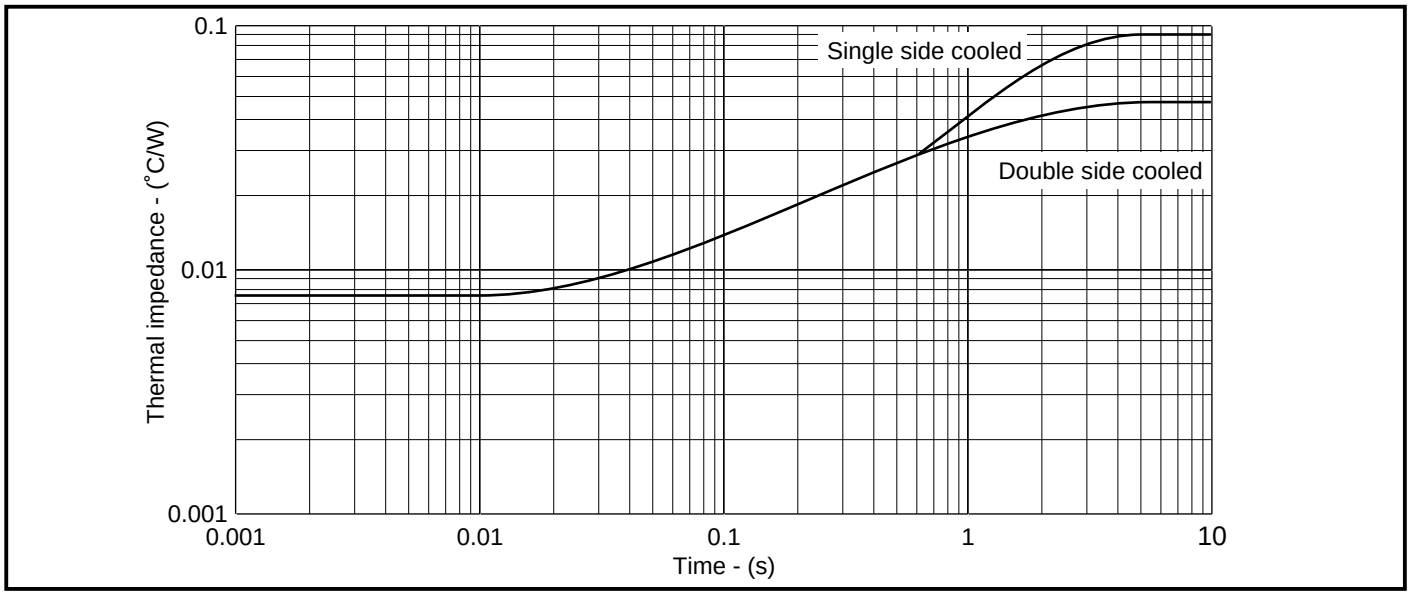
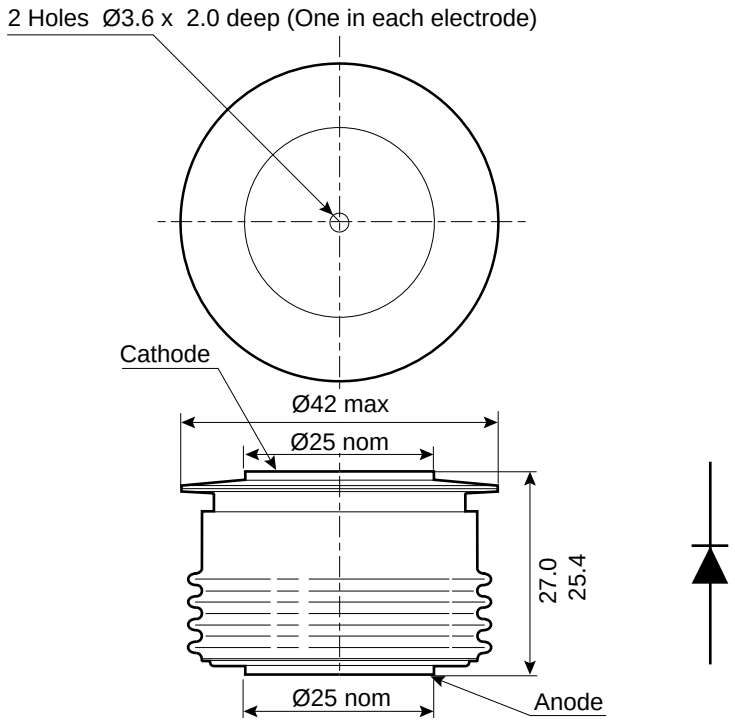


Fig.6 Maximum (limit) transient thermal impedance - junction to case - (˚C/W)

PACKAGE DETAILS

For further package information, please contact Customer Services. All dimensions in mm, unless stated otherwise.
DO NOT SCALE.



Nominal weight: 160g
Clamping force: 8kN ±10%

Package outine type code: K

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The Power Assembly group was set up to provide a support service for those customers requiring more than the basic semiconductor, and has developed a flexible range of heatsink and clamping systems in line with advances in device voltages and current capability of our semiconductors.

We offer an extensive range of air and liquid cooled assemblies covering the full range of circuit designs in general use today. The Assembly group offers high quality engineering support dedicated to designing new units to satisfy the growing needs of our customers.

Using the latest CAD methods our team of design and applications engineers aim to provide the Power Assembly Complete Solution (PACs).

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The Power Assembly group has its own proprietary range of extruded aluminium heatsinks which have been designed to optimise the performance of Dynex semiconductors. Data with respect to air natural, forced air and liquid cooling (with flow rates) is available on request.

For further information on device clamps, heatsinks and assemblies, please contact your nearest sales representative or Customer Services.

DYNEX SEMICONDUCTOR

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Preliminary Information: The product is in design and development. The datasheet represents the product as it is understood but details may change.

Advance Information: The product design is complete and final characterisation for volume production is well in hand.

No Annotation: The product parameters are fixed and the product is available to datasheet specification.